


Type	Ag* Al*	V _{RRM} [V]	I _F [A]	Chip Size [mm] x [mm]	Package Options
DWLP 23	<input checked="" type="checkbox"/> <input checked="" type="checkbox"/>	600	30	5.50 3.50	sawn on foil <input checked="" type="checkbox"/> unsawn wafer <input checked="" type="checkbox"/> * in wafer pack <input checked="" type="checkbox"/>

*Frontside options

*Please contact IXYS chip sales



Mechanical Parameters

Area active	11.08	mm ²
Area total	19.25	mm ²
Wafer size Ø	150	mm
Thickness	365	µm
Material	Si	
Max. possible chips per wafer	770	
Passivation front side	Glass	
Metallization top side	bondable or solderable	
Metallization backside	solderable (only): Al / Ti / Ni / Ag	
Recom. wire bonds (Al)	Anode	Number 4
		Ø 380 µm
Reject Ink Dot Size		Ø 0.4-1.0 mm
Recom. Storage Environment		
sawn on foil	in org. container, in dry nitrogen	< 6 month
unsawn wafer	in org. container, in dry nitrogen	< 2 year
in wafer pack	in org. container, in dry nitrogen	< 2 year
	T _{stg}	-40 ... 40 °C

Features:

- Anode top
- Pt doped
- Epitaxial diode
- Planar surface
- Glass passivated

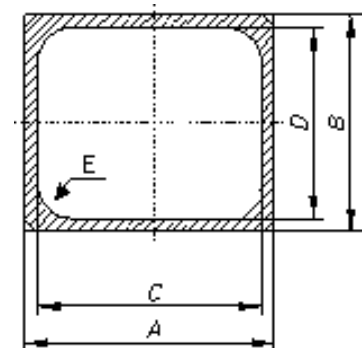
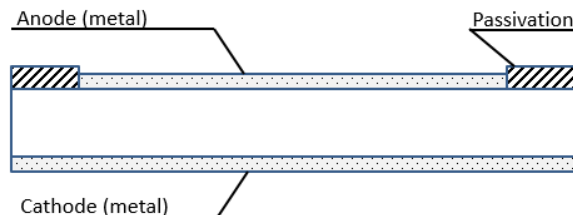
Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders
- PDP

*Sinterable top/bottom side on request

Dimensions

A	B	C	D	E
[mm]	[mm]	[mm]	[mm]	[mm]
5.50	3.50	4.50	2.50	0.20



Electrical parameters

Symbol	Conditions	Ratings		
		min.	typ.	max.
I_R	$V = V_{RRM}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$			10 μA
				0.2 mA
V_F	$I_F = 30\text{ A}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$			1.54 V
				1.18 V
V_{FO}	For power-loss calculations only			0.91 V
r_F	$T_{VJ} = 175^\circ\text{C}$			6.10 m Ω
T_{VJ}		-55		175 $^\circ\text{C}$
$I_{F(AV)}$ *	$T_C = 125^\circ\text{C}; 180^\circ\text{ rect.}$			30 A
I_{FSM} *	$T_{VJ} = 45^\circ\text{C}; t = 10\text{ ms (50 Hz), sine}$			250 A
R_{thJC} *	DC current			0.9 K/W
t_{rr}	$V_R = 30$ $I_F = 1\text{ A}; -di_F/dt = 200\text{ A}/\mu\text{s}; T_{VJ} = 25^\circ\text{C}$		35	ns
I_{RM}	$V_R = 100$ $I_F = 50\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; T_{VJ} = 25^\circ\text{C}$		3.00	3.50 A

* Data according to assembled Chip

Data according to IEC 60747

Terms of Conditions and Usage

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Should you intend to use the product in aviation applications, in health or life endangering or life support applications, please notify. For any such applications we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures to ensure application specific product capabilities and notify that IXYS may delivery dependent on the realization of any such measures.